1500V, 3.0Ω, 9A, N-Channel



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Features

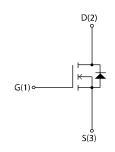
- Low On-Resistance
- Ultra High Voltage
- Pb-Free and RoHS Compliance

Power MOSFET

- High Speed Switching
- 100% Avalanche Tested

Electrical Connection

N-Channel



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter		Symbol	Value	Unit
Drain to Source Voltage		V _{DSS}	1500	V
Gate to Source Voltage		VGSS	±30	V
Drain Current (DC)		ID	9	Α
Drain Current (DC) Limited by Package		I _{DL}	6	Α
Drain Current (Pulse) PW ≤ 10μs, duty cycle ≤ 1%		I _{DP}	18	А
Dower Dissipation		Do	3.0	W
Power Dissipation	Tc=25°C	PD	78	
Junction Temperature		Tj	150	°C
Storage Temperature		Tstg	−55 to +150	°C
Source Current (Body Diode)		IS	6	Α
Avalanche Energy (Single Pulse) *1		EAS	197	mJ
Lead Temperature for Soldering Purposes, 3 mm from case for 10 seconds		TL	260	°C

Marking

09N150 LOT No







Thermal Resistance Ratings

Parameter	Symbol	Value	Unit	
Junction to Case Steady State	$R_{\theta JC}$	1.60	0000	
Junction to Ambient *2	R _{0.IA}	41.7	°C/W	

Note : *1 V_{DD} =50V, L=10mH, I_{AV} =6A (Fig.1)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

^{*2} Insertion mounted

Electrical Characteristics at Ta = 25°C

Parameter	Cumbal	Condition -	Value			1.1-24
Parameter	Symbol	Symbol Conditions		typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	1500			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =1200V, V _{GS} =0V			1	mA
Gate to Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =10V, I _D =1mA	2		4	٧
Forward Transconductance	9FS	V _{DS} =20V, I _D =3A		5.2		S
Static Drain to Source On-State Resistance	R _{DS} (on)	I _D =3A, V _{GS} =10V		2.2	3.0	Ω
Input Capacitance	Ciss			2025		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		222		pF
Reverse Transfer Capacitance	Crss			66		pF
Turn-ON Delay Time	t _d (on)			33		ns
Rise Time	t _r	See Fig.2		75		ns
Turn-OFF Delay Time	t _d (off)			500		ns
Fall Time	tf			111		ns
Total Gate Charge	Qg			114		nC
Gate to Source Charge	Qgs V _{DS} =200V, V _{GS} =10V, I _D =6A	V _{DS} =200V, V _{GS} =10V, I _D =6A		12		nC
Gate to Drain "Miller" Charge	Qgd			57		nC
Forward Diode Voltage	V _{SD}	I _S =6A, V _{GS} =0V		0.8	1.5	٧
Reverse Recovery Time	t _{rr}	See Fig.3		1050		ns
Reverse Recovery Charge	ry Charge Q _{rr} I _S =6A, V _G S=0V, di/dt=10			9010		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Fig.1 : Unclamped Inductive Switching Test Circuit

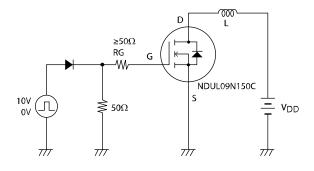


Fig.3 : Reverse Recovery Time Test Circuit

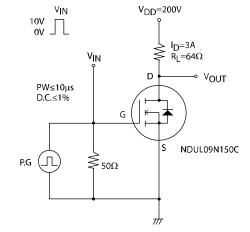
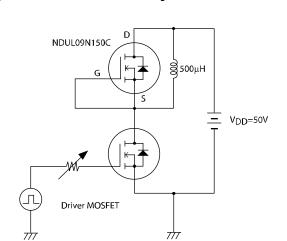
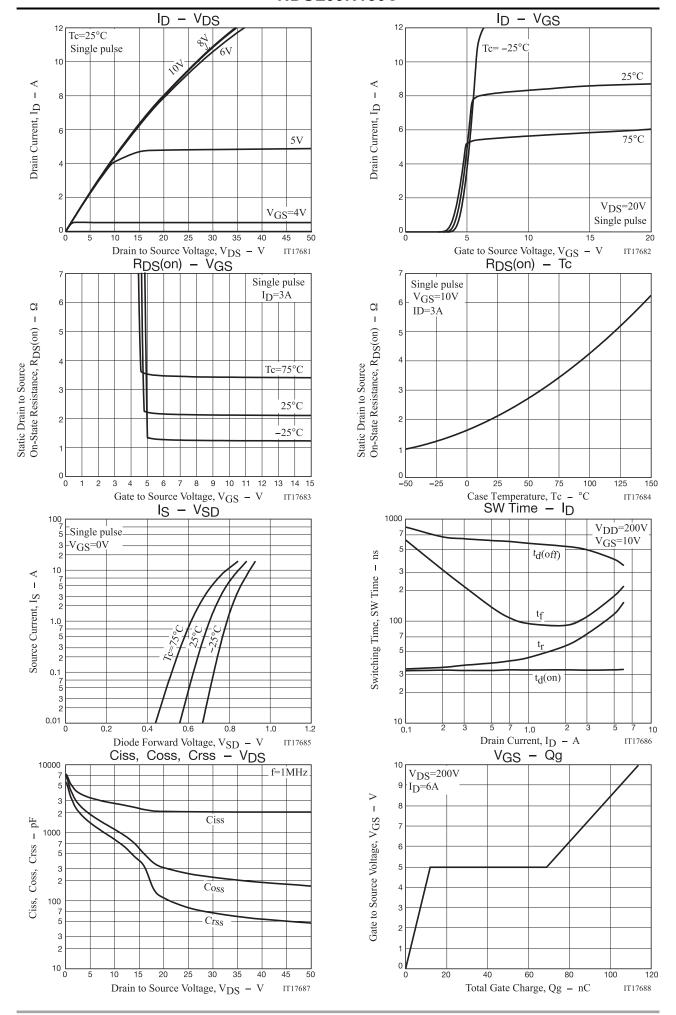
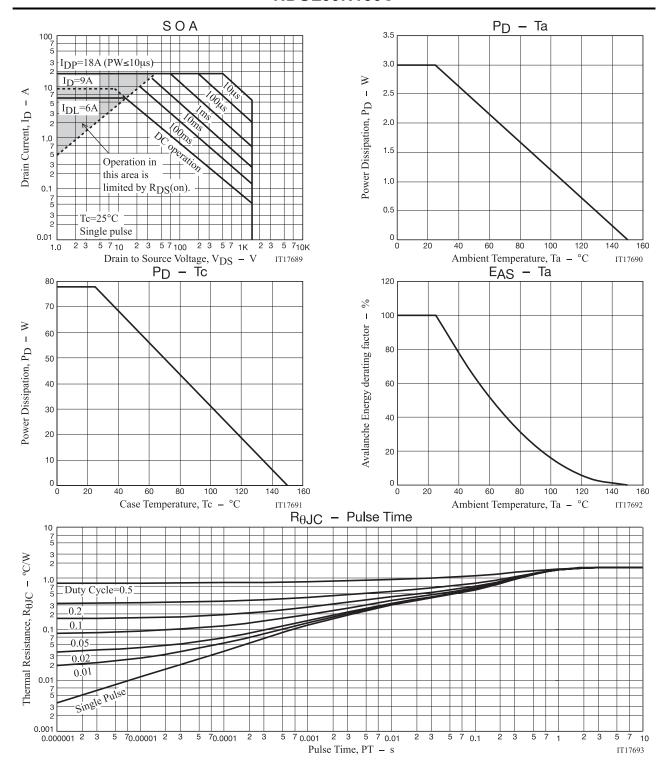


Fig.2: Switching Time Test Circuit





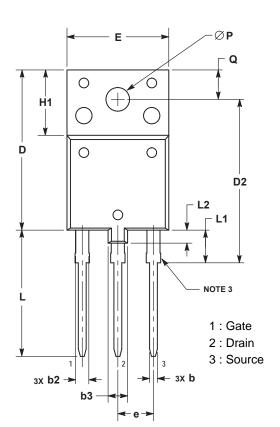


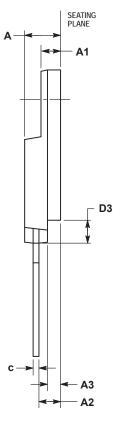
Package Dimensions

NDUL09N150CG

unit: mm

TO-3PF-3L CASE 340AH **ISSUE A**





- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- CONTROLLING DIMENSION: MILLIMETERS.
 CONTOUR UNCONTROLLED IN THIS AREA (6 PLACES).
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE, THESE DIMENSIONS ARE TO BE MEA. SURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION.
- LEAD WIDTH INCLUDING PROTRUSION SHALL NOT EXCEED 2.20.

	MILLIMETERS		
DIM	MIN	MAX 5.70	
Α	5.30		
A1	2.80	3.20	
A2	3.10	3.50	
A3	1.80	2.20	
b	0.65	0.95	
b2	1.90	2.15	
b3	3.80	4.20	
С	0.80	1.10	
D	24.30	24.70	
D2	24.70	25.30	
D3	3.30	3.70	
Е	15.30	15.70	
е	5.35	5.55	
H1	9.80	10.20	
L	19.10	19.50	
L1	4.80	5.20	
L2	1.90	2.20	
Р	3.40	3.80	
Q	4.30	4.70	

ORDERING INFORMATION

Device	Package	Shipping	Note
NDUL09N150CG	TO-3PF-3L SC-94	30pcs. / Tube	Pb-Free

Note on usage: Since the NDUL09N150C is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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